

## CLAIMS

### WHAT IS CLAIMED:

1. A method comprising:
- measuring at least one parameter characteristic of processing performed on a  
workpiece in a processing step;
- modeling the at least one characteristic parameter measured using a correlation  
model; and
- applying the correlation model to modify the processing performed in the  
processing step.

2. The method of claim 1, wherein measuring the at least one parameter characteristic of the processing performed on the workpiece in the processing step comprises measuring the at least one characteristic parameter at a wafer electrical test (WET).

3. The method of claim 1, wherein measuring the at least one parameter characteristic of the processing performed on the workpiece in the processing step comprises measuring the at least one parameter characteristic of rapid thermal processing performed on the workpiece in a rapid thermal processing step.

4. The method of claim 2, wherein measuring the at least one parameter characteristic of the processing performed on the workpiece in the processing step comprises measuring the at least one parameter characteristic of rapid thermal processing performed on the workpiece in a rapid thermal processing step.

5. The method of claim 1, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

5 6. The method of claim 2, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

7. The method of claim 3, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

8. The method of claim 5, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises applying the wafer electrical test (WET) correlation model to modify rapid thermal processing performed on the workpiece in a rapid thermal processing step.

9. The method of claim 6, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises applying the wafer electrical test (WET) correlation model to modify rapid thermal processing performed on the workpiece in a rapid thermal processing step.

10. The method of claim 7, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises

applying the wafer electrical test (WET) correlation model to modify the rapid thermal processing performed on the workpiece in the rapid thermal processing step.

11. A computer-readable, program storage device, encoded with instructions that,  
5 when executed by a computer, perform a method comprising:

measuring at least one parameter characteristic of processing performed on a  
workpiece in a processing step;

modeling the at least one characteristic parameter measured using a correlation  
model; and

10 applying the correlation model to modify the processing performed in the  
processing step.

12. The device of claim 11, wherein measuring the at least one parameter  
characteristic of the processing performed on the workpiece in the processing step comprises  
15 measuring the at least one characteristic parameter at a wafer electrical test (WET).

13. The device of claim 11, wherein measuring the at least one parameter  
characteristic of the processing performed on the workpiece in the processing step comprises  
measuring the at least one parameter characteristic of rapid thermal processing performed on  
20 the workpiece in a rapid thermal processing step.

14. The device of claim 12, wherein measuring the at least one parameter  
characteristic of the processing performed on the workpiece in the processing step comprises  
measuring the at least one parameter characteristic of rapid thermal processing performed on  
25 the workpiece in a rapid thermal processing step.

15. The device of claim 11, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

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16. The device of claim 12, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

10 17. The device of claim 13, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

15 18. The device of claim 15, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises applying the wafer electrical test (WET) correlation model to modify rapid thermal processing performed on the workpiece in a rapid thermal processing step.

20 19. The device of claim 16, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises applying the wafer electrical test (WET) correlation model to modify rapid thermal processing performed on the workpiece in a rapid thermal processing step.

25 20. The device of claim 17, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises

applying the wafer electrical test (WET) correlation model to modify the rapid thermal processing performed on the workpiece in the rapid thermal processing step.

21. A computer programmed to perform a method comprising:

5 measuring at least one parameter characteristic of processing performed on a workpiece in a processing step;  
modeling the at least one characteristic parameter measured using a correlation model; and  
applying the correlation model to modify the processing performed in the  
10 processing step.

22. The computer of claim 21, wherein measuring the at least one parameter characteristic of the processing performed on the workpiece in the processing step comprises measuring the at least one characteristic parameter at a wafer electrical test (WET).

15 23. The computer of claim 21, wherein measuring the at least one parameter characteristic of the processing performed on the workpiece in the processing step comprises measuring the at least one parameter characteristic of rapid thermal processing performed on the workpiece in a rapid thermal processing step.

20 24. The computer of claim 22, wherein measuring the at least one parameter characteristic of the processing performed on the workpiece in the processing step comprises measuring the at least one parameter characteristic of rapid thermal processing performed on the workpiece in a rapid thermal processing step.

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25. The computer of claim 21, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

5 26. The computer of claim 22, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

10 27. The computer of claim 23, wherein modeling the at least one characteristic parameter measured using the correlation model comprises modeling the at least one characteristic parameter measured using a wafer electrical test (WET) correlation model.

15 28. The computer of claim 25, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises applying the wafer electrical test (WET) correlation model to modify rapid thermal processing performed on the workpiece in a rapid thermal processing step.

20 29. The computer of claim 26, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises applying the wafer electrical test (WET) correlation model to modify rapid thermal processing performed on the workpiece in a rapid thermal processing step.

30. The computer of claim 27, wherein applying the wafer electrical test (WET) correlation model to modify the processing performed in the processing step comprises

applying the wafer electrical test (WET) correlation model to modify the rapid thermal processing performed on the workpiece in the rapid thermal processing step.